UNR1231/1231A (UN1231/1231A)

Silicon NPN epitaxial planar transistor

For amplification of the low frequency

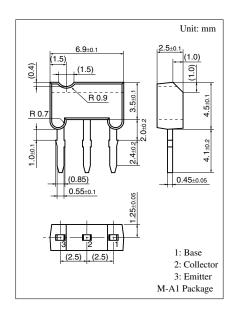
Features

- High forward current transfer ratio h_{FE}
- M type mold package
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit	
Collector to base voltage	UNR1231	V	20	V	
	UNR1231A	V_{CBO}	60	•	
Collector to emitter voltage	UNR1231	V_{CEO}	20	V	
	UNR1231A	V CEO	50	•	
Collector current		I_{C}	0.7	A	
Peak collector current		I_{CP}	1.5	A	
Total power dissipation		P_T^*	1.0	W	
Junction temperature		T_{j}	150	°C	
Storage temperature		T_{stg}	-55 to +150	°C	

^{*} Printed circuit board: Copper foil area of 1cm² or more and thickness of 1.7mm for the collector portion.



Internal Connection

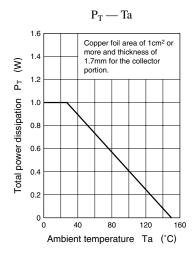
Electrical Characteristics (Ta=25°C)

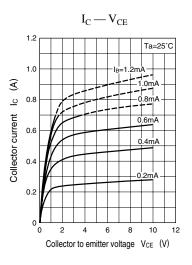
Parameter		Symbol	Conditions	min	typ	max	Unit
Collector cutoff current		I _{CBO}	$V_{CB} = 15V, I_E = 0$			1	μΑ
		I _{CEO}	$V_{CE} = 15V, I_{B} = 0$			10	μΑ
Emitter cutoff current		I _{EBO}	$V_{EB} = 14V, I_C = 0$			0.5	mA
Collector to base voltage	UNR1231	- V _{CBO}	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	20			V
	UNR1231A			60			
Collector to emitter voltage	UNR1231	V _{CEO}	$I_C = 1 \text{mA}, I_B = 0$	20			· V
	UNR1231A			50			
Forward current transfer ratio h _F		h _{FE}	$V_{CE} = 10V, I_{C} = 150 \text{mA*}$	800		2100	
Collector to emitter saturation voltage $V_{CE(sat)}$		$I_C = 100 \text{mA}, I_B = 5 \text{mA}^*$			0.4	V	
Input resistance R ₁		R ₁		0.7	1	1.3	kΩ
Resistance ratio		R ₁ /R ₂			0.021		

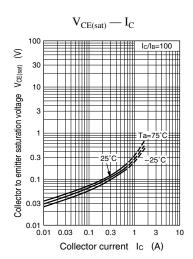
*Pulse measurement

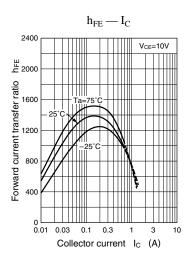
Note) The part numbers in the parenthesis show conventional part number.

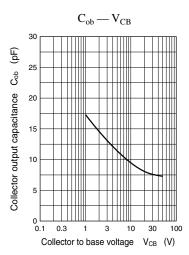
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